

 H. Display and Imaging Technologies 분과

2019년 2월 14일(목), 11:00-12:30

Room H (루비1+2, 5층)

[TH2-H] Thin Film Transistor & Encapsulation for Display Applications

좌장: 배병성 교수(호서대학교), 황도경 박사(KIST)

<p>TH2-H-1 11:00-11:30</p>	<p>[초청] Structure, Stability, and Applications of InGaZnO Thin-Film Transistors Saeroonter Oh <i>Department of Electrical Engineering, Hanyang University</i></p>
<p>TH2-H-2 11:30-11:45</p>	<p>Channel Geometry Effects on the Bias-Stress Stabilities of Flexible InGaZnO Thin Film Transistors under Mechanical Stress Conditions Hye-Won Jang, Hyeong-Rae Kim, Ji-Hee Yang, and Sung-Min Yoon <i>Department of Advanced Materials Engineering for Information and Electronics, Kyung Hee University</i></p>
<p>TH2-H-3 11:45-12:00</p>	<p>Effect of Zirconium Oxide-Silicon Oxide Nano Laminate Gate Dielectrics in TFT MinJung Kim¹, WanHo Choi², Jiazhen Sheng², Hyun-Jun Jeong², and Jin-Seong Park^{1,2} ¹<i>Division of Nanoscale Semiconductor Engineering, Hanyang University,</i> ²<i>Division of Materials Science and Engineering, Hanyang University</i></p>
<p>TH2-H-4 12:00-12:15</p>	<p>Electrical Properties of Novel P-Type Setezn Thin Film Transistor Taeyoon Kim¹, Gabiel Jang¹, Daseul Hyun¹, Mihyun Park¹, JungYup Yang², and JinPyo Hong¹ ¹<i>Novel Functional Materials and Devices Lab, Department of Physics, Hanyang University,</i> ²<i>Department of Physics, Kunsan National University</i></p>
<p>TH2-H-5 12:15-12:30</p>	<p>Influence of Cation Compositions in InGaZnO Active Channel Prepared by Atomic-Layer Deposition on Thin-Film Transistor Characteristics Seung-Bo Ko¹, Nak-Jin Seong², Kyujeong Choi², Se-Na Choi¹, So-Jung Yoon¹, and Sung-Min Yoon¹ ¹<i>Department of Advanced Materials Engineering for Information and Electronics, Kyung Hee University,</i> ²<i>NCD Co. Ltd</i></p>